

# MOS FET FJ6K01010L

# FJ6K01010L Silicon P-channel MOS FET

### For switching

#### Features

- Low drain-source On-state resistance : RDS (on) typ. = 26 m $\Omega$  (VGS = -4.5 V)
- Low drive voltage : 1.8 V drive
- Halogen-free / RoHS compliant
- (EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)

■ Absolute Maximum Ratings Ta = 25 °C

Parameter

Marking Symbol : T4

Drain-source voltage

Gate-source voltage

Pulse drain current

Total power dissipation

Operating ambient temperature

Channel temperature

Storage temperature

Drain current

Revised

#### Packaging

Embossed type (Thermo-compression sealing): 3 000 pcs / reel (standard)

Note) \*1 Measuring on Glass epoxy board (25.4 x 25.4 x 0.8 mm) (See Figure 1) Absolute maximum rating without heat sink for PD is 150 mW

Symbol

VDS

VGS

ID

IDp

PD

Tch

Topr

Tstg

Rating

-12

±8

-4.0

-20

700

150

-40 to + 85

-55 to +150

Unit

V

V

А

А

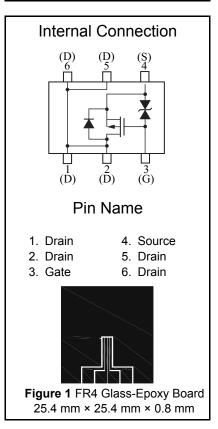
mW

°C

°C

°C

|                                 | Unit : mm                         |  |  |  |  |
|---------------------------------|-----------------------------------|--|--|--|--|
|                                 |                                   |  |  |  |  |
| 1. Drain<br>2. Drain<br>3. Gate | 4. Source<br>5. Drain<br>6. Drain |  |  |  |  |
| Panasonic                       | WSMini6-F1-B                      |  |  |  |  |
| JEITA                           | SC-113DA                          |  |  |  |  |
| Code                            | _                                 |  |  |  |  |



## Established : 2010-04-05 : 2013-07-01



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| Electrical Characteristics | Ta = 25 °C ± 3 °C |
|----------------------------|-------------------|
|----------------------------|-------------------|

| Parameter                         | Symbol   | Conditions                      | Min  | Тур   | Max  | Unit |
|-----------------------------------|----------|---------------------------------|------|-------|------|------|
| Drain-source breakdown voltage    | VDSS     | ID = -1 mA, VGS = 0             | -12  |       |      | V    |
| Drain-source cutoff current       | IDSS     | VDS = -10 V, VGS = 0            |      |       | -1.0 | μA   |
| Gate-source cutoff current        | IGSS     | VGS = ±8 V, VDS = 0             |      |       | ±10  | μA   |
| Gate threshold voltage            | Vth      | ID = -1.0 mA, VDS = -6.0 V      | -0.3 | -0.65 | -1.0 | V    |
|                                   | RDS(on)1 | - )                             |      | 26    | 34   |      |
| Drain-source ON resistance        | RDS(on)2 | ID = -0.5 A, VGS = -2.5 V       |      | 30    | 41   | mΩ   |
|                                   | RDS(on)3 | ID = -0.5 A, VGS = -1.8 V       |      | 36    | 54   | I    |
| Forward transfer admittance       | Yfs      | ID = -1.0 A, VDS = -10 V        | 4.0  |       |      | S    |
| Input capacitance                 | Ciss     | VDS = -10 V, VGS = 0, f = 1 MHz |      | 1 400 |      | pF   |
| Output capacitance                | Coss     |                                 |      | 190   |      | pF   |
| Reverse transfer capacitance      | Crss     |                                 |      | 210   |      | pF   |
| Turn-on delay time <sup>*1</sup>  | td(on)   | VDD = -6 V, VGS = 0 to -4 V     |      | 9     |      | ns   |
| Rise time *1                      | tr       | ID = -1.0 A                     |      | 40    |      | ns   |
| Turn-off delay time <sup>*1</sup> | td(off)  | VDD = -6 V, VGS = -4 to 0 V     |      | 250   |      | ns   |
| Fall time <sup>*1</sup>           | tf       | ID = -1.0 A                     |      | 150   |      | ns   |

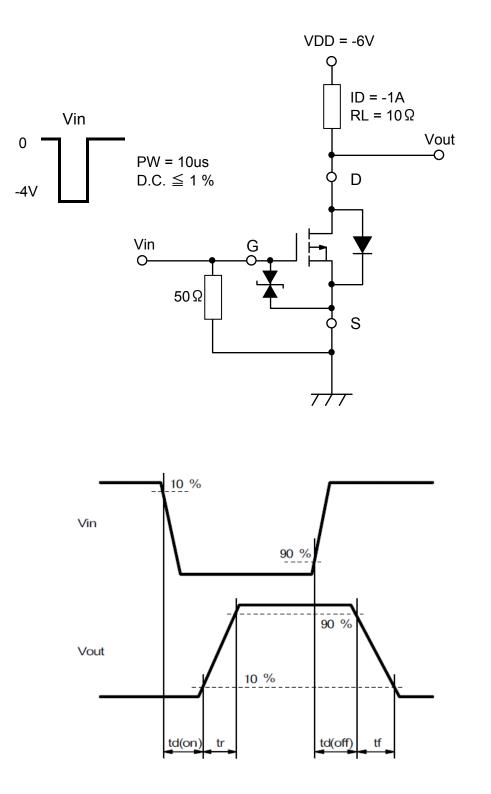
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

2. \*1 Measurement circuit for Turn-on Delay Time/Rise Time/Turn-off Delay Time/Fall Time

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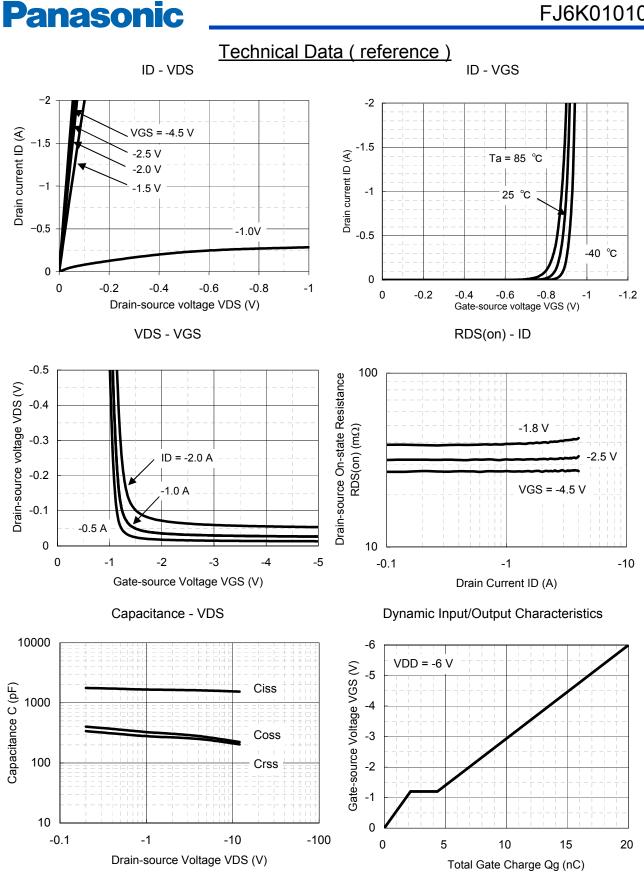


\*1 Measurement circuit for Turn-on Delay Time/Rise Time/Turn-off Delay Time/Fall Time



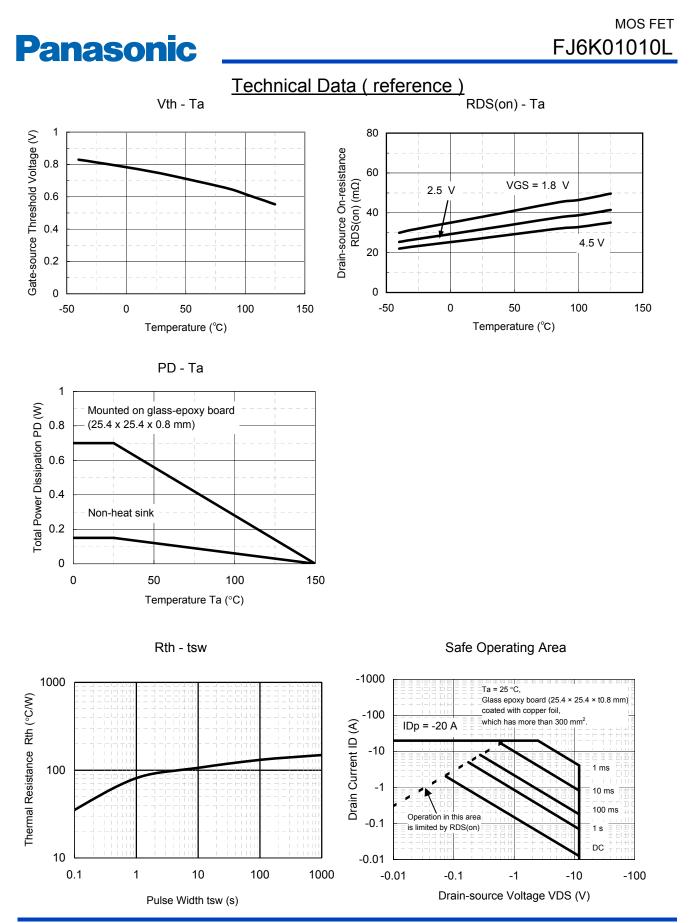
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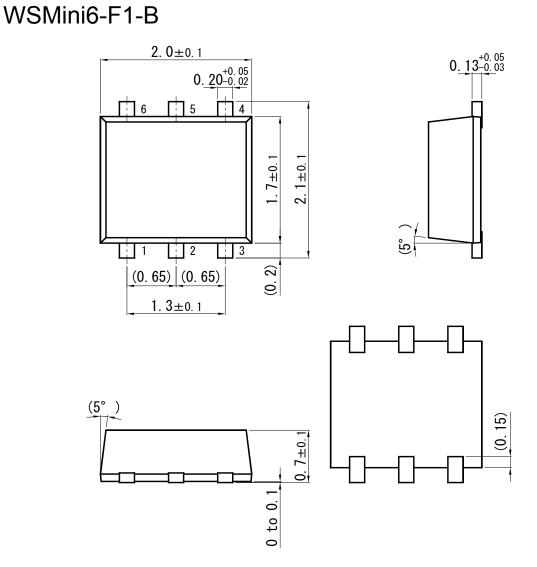




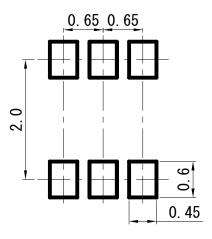
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Land Pattern (Reference) (Unit : mm)



Unit : mm

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